

*ABSTRACT AMENDMENTS*

Replace the Abstract with:

A porous MSQ is formed on a silicon substrate, and an SIC mask is formed thereon. Plasma etching, using the SIC mask as a mask, is performed to form a trench in the porous MSQ. A fluorinated polyxylilene film is formed on the entire surface of the substrate ~~+,~~ including the side surfaces of the trench, and the unnecessary fluorinated polyxylilene film ~~formed, on the area areas~~ other than the side surfaces of the trench, is removed. A barrier-metal film and a seed Cu layer are formed in the trench and a Cu is deposited.